T Gregorkiewicz

List of Publications by Year
in descending order

152	3,127	185998 28	182168 51
papers	citations	h-index	g-index

153	153	153	2231
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Hot-carrier-mediated impact excitation of Er3+ ions in SiO2 sensitized by Si Nanocrystals. Applied Physics Letters, 2018, 113, 031109.	1.5	11
2	High-Power Eu-Doped GaN Red LED Based on a Multilayer Structure Grown at Lower Temperatures by Organometallic Vapor Phase Epitaxy. MRS Advances, 2017, 2, 159-164.	0.5	18
3	Trapping time of excitons in Si nanocrystals embedded in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="bold">SiO</mml:mi><mml:mn mathvariant="bold">2</mml:mn></mml:msub></mml:math> matrix. Physical Review B, 2017, 95, .	1.1	5
4	Strong infrared photoluminescence in highly porous layers of large faceted Si crystalline nanoparticles. Scientific Reports, 2016, 6, 25664.	1.6	11
5	Step-like increase of quantum yield of 1.5â€‰Î¼m Er-related emission in SiO2 doped with Si nanocrystals. Journal of Applied Physics, 2015, 117, 064303.	1.1	1
6	Generation of hot carriers for photon management in future photovoltaics. Solar Energy Materials and Solar Cells, 2015, 135, 67-71.	3.0	6
7	Silicon quantum dots: surface matters. Journal of Physics Condensed Matter, 2014, 26, 173201.	0.7	163
8	Efficient optical extraction of hot-carrier energy. Nature Communications, 2014, 5, 4665.	5.8	42
9	Enhancement of luminescence quantum yield of 1.5 Âµm emission from Er-doped SiO2 sensitized with Si nanocrystals. Materials Research Society Symposia Proceedings, 2014, 1592, 1.	0.1	0
10	Optical excitation and external photoluminescence quantum efficiency of Eu3+ in GaN. Scientific Reports, 2014, 4, 5235.	1.6	33
11	Carrier dynamics in Si nanocrystals in an SiO2matrix investigated by transient light absorption. Physical Review B, 2013, 88, .	1.1	17
12	Thermally Activated Emission from Direct Bandgap-Like Silicon Quantum Dots. ECS Journal of Solid State Science and Technology, 2013, 2, R97-R99.	0.9	6
13	Manipulating Photon Energy with Si Nanocrystals. , 2012, , .		0
14	Si nanocrystals for photon management. , 2012, , .		0
15	Investigation of saturation and excitation behavior of 1.5 Î¼m emission from Er³⁺ ions in SiO₂ sensitized with Si nanocrystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2312-2317.	0.8	3
16	Self-trapped exciton state in Si nanocrystals revealed by induced absorption. Physical Review B, 2012, 85, .	1.1	22
17	Increased carrier generation rate in Si nanocrystals in SiO2 investigated by induced absorption. Applied Physics Letters, 2011, 99, .	1.5	19
18	Step-like enhancement of luminescence quantum yield of silicon nanocrystals. Nature Nanotechnology, 2011, 6, 710-713.	15.6	186

#	Article	IF	Citations
19	Evaluation of free carrier losses to 1.54Î¼m emission in Si/Si:Er nanolayers on SOI substrate for optical gain observation. Optical Materials, 2011, 33, 1094-1096.	1.7	2
20	Fast dynamics of 1.5Î¼m photoluminescence in Er-doped SiO2 sensitized with Si nanocrystals. Optical Materials, 2011, 33, 1091-1093.	1.7	0
21	Dynamics and microscopic origin of fast 1.5<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Î¼</mml:mi></mml:mrow></mml:math>m emission in Er-doped SiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>sensitized Si	1.1	9
22	Photon cutting for excitation of Er3+ions in SiO2sensitized by Si quantum dots. Physical Review B, 2011, 84, .	1.1	15
23	Saturation of luminescence from Si nanocrystals embedded in SiO₂. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 183-187.	0.8	27
24	Direct bandgap optical transitions in Si nanocrystals. JETP Letters, 2010, 90, 758-762.	0.4	59
25	Red spectral shift and enhanced quantum efficiency in phonon-free photoluminescence from silicon nanocrystals. Nature Nanotechnology, 2010, 5, 878-884.	15.6	294
26	Optical gain of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>1.54</mml:mn><mml:mtext>â€,</mml:mtext><mml:mi>Î¼</mml:mi><mml:mtext>	1.1	17
27	Terahertz electromagnetic transitions observed within theI415/2ground multiplet ofEr3+ions in Si. Physical Review B, 2009, 79, .	1.1	2
28	Space-separated quantum cutting in differently prepared solid-state dispersions of Si nanocrystals and Er3+ ions in SiO2. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 87-89.	1.7	4
29	Optical properties of Si/Si:Er multi-nanolayer structures grown by SMBE method. Physica B: Condensed Matter, 2009, 404, 5132-5135.	1.3	0
30	Optical spectroscopy of carrier relaxation processes in Si nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 190-193.	1.7	8
31	On relation between the 1.5Î¼m Er-related emission and 9Î¼m vibrational modes of oxygen in silicon. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 1052-1054.	1.3	0
32	Excitation efficiency and saturation dynamics of near-infrared emission from Si nanocrystals embedded in a SiO2-matrix. Journal of Physics: Conference Series, 2009, 165, 012018.	0.3	1
33	Pump-probe investigations of THz transitions in Si/Si:Er3+ nanolayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 160-162.	1.7	0
34	Mid-infrared spectroscopy of the Er-related donor state in Si/Si:Er3+ nanolayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 131-134.	1.7	0
35	Space-separated quantum cutting with silicon nanocrystals for photovoltaic applications. Nature Photonics, 2008, 2, 105-109.	15.6	302
36	Energy transfer in Er-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>SiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn	1.1	70

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37	Microscopic evidence for role of oxygen in luminescence ofEr3+ions in Si: Two-color and pump-probe spectroscopy. Physical Review B, 2008, 78, .	1.1	10
38	Concentration ofEr3+ions contributing to1.5âˆ¼Î¼memission inSiâ•Si:Ernanolayers. Physical Review B, 2007, 76, .	1.1	21
39	Donor-State-Enabling Er-Related Luminescence in Silicon: Direct Identification and Resonant Excitation. Physical Review Letters, 2007, 99, 077401.	2.9	29
40	Non-radiative sub-microsecond recombination of excited Er3+ ions in SiO2 sensitized with Si nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 144-147.	1.3	7
41	1.54Î¼m Si:Er light emitting diode with memory function. Applied Physics Letters, 2006, 88, 201101.	1.5	4
42	On optical activity of Er3+ ions in Si-rich SiO2 waveguides. Applied Physics Letters, 2006, 89, 171908.	1.5	15
43	Nanosecond Dynamics of the Near-Infrared Photoluminescence of Er-DopedSiO2Sensitized with Si Nanocrystals. Physical Review Letters, 2006, 97, 207401.	2.9	87
44	Isotope Dependence of the Lifetime of the1136âˆ’cmâˆ’1Vibration of Oxygen in Silicon. Physical Review Letters, 2006, 96, 225503.	2.9	34
45	Photoluminescence excitation spectroscopy of erbium in epitaxially grown Si:Er structures. Optical Materials, 2005, 27, 890-893.	1.7	9
46	Erbium Photoluminescence Excitation Spectroscopy in Si : Er Epitaxial Structures. Physics of the Solid State, 2005, 47, 86.	0.2	3
47	Erbium Excitation in a SiO[sub 2] : Si-nc Matrix under Pulsed Pumping. Physics of the Solid State, 2005, 47, 110.	0.2	1
48	The Auger process of luminescence quenching in Si/Si:Er multinanolayers. Journal of Physics Condensed Matter, 2005, 17, S2191-S2195.	0.7	7
49	Theoretical modeling of thermally activated luminescence quenching processes in Si:Er. Physical Review B, 2005, 72, .	1.1	15
50	Terahertz modulation of the blue photoluminescence in ZnSe. Physical Review B, 2005, 72, .	1.1	7
51	Time-resolved free-electron laser spectroscopy of a copper isoelectronic center in silicon. Physical Review B, 2005, 71, .	1.1	8
52	On 2.7 Î½m Emission from Er-doped Large Bandgap Hosts. Materials Research Society Symposia Proceedings, 2005, 866, 7.	0.1	6
53	Sensitization of Er luminescence by Si nanoclusters. Physical Review B, 2004, 69, .	1.1	131
54	Optical properties of a single type of optically active center inSiâ•Si:Ernanostructures. Physical Review B, 2004, 70, .	1.1	33

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55	Terahertz-assisted excitation of the1.5â˜Î¼photoluminescence ofErin crystallineSi. Physical Review B, 2004, 70, .	1.1	6
56	Er3+ photoluminescence excitation spectra in erbium-doped epitaxial silicon structures. Physics of the Solid State, 2004, 46, 97-100.	0.2	11
57	Photoluminescence and excitation spectroscopy of the 1.5Â Î¼m Er-related band in MBE-grown GaN layers. Superlattices and Microstructures, 2004, 36, 701-705.	1.4	5
58	Excitation paths in RE-doped IIIâ€“V semiconductors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 141-145.	1.7	12
59	Spectroscopic characterization of Er-1 center in selectively doped silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 150-152.	1.7	0
60	Two-color mid-infrared spectroscopy of optically doped semiconductors. Journal of Luminescence, 2003, 102-103, 85-90.	1.5	8
61	Silicon-based all-optical memory elements for 1.54 Î¼m photonics. Solid-State Electronics, 2003, 47, 165-168.	0.8	4
62	Photoluminescence quenching in InP:Yb with a free-electron laser. Applied Surface Science, 2003, 208-209, 23-26.	3.1	1
63	Magneto-optical study of Er+3-related center in selectively doped Si:Er. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 544-546.	1.3	4
64	Optical properties of a silver-related defect in silicon. Physical Review B, 2003, 67, .	1.1	15
65	Microscopic Structure of Er-Related Optically Active Centers in Crystalline Silicon. Physical Review Letters, 2003, 90, 066401.	2.9	50
66	Auger deexcitation ofEr3+ions in crystalline Si optically induced by midinfrared illumination. Physical Review B, 2003, 68, .	1.1	15
67	Microscopic model for nonexcitonic mechanism of 1.5-Î¼m photoluminescence of theEr3+ion in crystalline Si. Physical Review B, 2003, 67, .	1.1	19
68	Si Nanocrystals as Sensitizers for Er PL in SiO2. Materials Research Society Symposia Proceedings, 2003, 770, 691.	0.1	2
69	Optically Induced Deexcitation of Rare-Earth Ions in a Semiconductor Matrix. Physical Review Letters, 2002, 89, 227401.	2.9	71
70	Afterglow effect in photoluminescence of Si:Er. Physical Review B, 2002, 65, .	1.1	28
71	Time-resolved investigation of the mid-infrared-induced enhancement of Er3+ emission in Si. Physica B: Condensed Matter, 2001, 308-310, 337-339.	1.3	0
72	Observation of Zeeman effect in photoluminescence of Er3+ ion imbedded in crystalline silicon. Physica B: Condensed Matter, 2001, 308-310, 340-343.	1.3	18

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73	Erbium excitation across the bulk of silicon wafer: an effect of pâ€“n junction at Si/Si:Er interface. Physica B: Condensed Matter, 2001, 308-310, 357-360.	1.3	0
74	Optically induced Auger recombination of Yb3+ in p-type InP. Physica B: Condensed Matter, 2001, 308-310, 884-887.	1.3	3
75	Photoluminescence from Si:Er under front and backside excitation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 59-61.	1.7	3
76	Mid-infrared induced quenching of photoluminescence in Si:Er. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 80-82.	1.7	0
77	Semiconductors: Rare Earth Impurities. , 2001, , 8392-8396.		0
78	Free-electron laser studies of energy transfer mechanisms in semiconductors doped with transition series ions. Journal of Luminescence, 2001, 94-95, 243-248.	1.5	8
79	Influence ofpâ^'njunction formation at a Si/Si:Er interface on low-temperature excitation ofEr3+ions in crystalline silicon. Physical Review B, 2001, 64, .	1.1	4
80	Excitation cross section of erbium in semiconductor matrices under optical pumping. Physical Review B, 2001, 64, .	1.1	51
81	780-meV photoluminescence band in silver-doped silicon: Isotope effect and time-resolved spectroscopy. Physical Review B, 2001, 65, .	1.1	8
82	Tracking recombination processes in Si : Er with a free-electron laser. Journal of Luminescence, 2000, 87-89, 96-100.	1.5	0
83	Hydrogen passivation of the selenium double donor in silicon:â€‚A study by magnetic resonance. Physical Review B, 2000, 61, 7448-7458.	1.1	7
84	Photoluminescence of erbium-doped silicon: Excitation power and temperature dependence. Journal of Applied Physics, 2000, 88, 1443-1455.	1.1	24
85	Energy transfer between shallow centers and rare-earth ion cores:Er3+ion in silicon. Physical Review B, 2000, 61, 5369-5375.	1.1	36
86	Lasing in Rare-Earth-Doped Semiconductors: Hopes and Facts. MRS Bulletin, 1999, 24, 27-32.	1.7	21
87	Direct spectral probing of energy storage in Si:Er by a free-electron laser. Applied Physics Letters, 1999, 75, 4121-4123.	1.5	28
88	Atomic and electronic structure of hydrogen-passivated double selenium donors in silicon. Physica B: Condensed Matter, 1999, 273-274, 239-242.	1.3	2
89	Spectroscopic probing of defect-related energy storage in silicon doped with erbium. Physica B: Condensed Matter, 1999, 273-274, 326-329.	1.3	1
90	The photoluminescence mechanism of erbium in silicon: intensity dependence on excitation power and temperature. Physica B: Condensed Matter, 1999, 273-274, 338-341.	1.3	2

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91	Role of Shallow Bound States in Emission Processes of Rare-Earth Doped Semiconductors. Physica Status Solidi (B): Basic Research, 1998, 210, 737-745.	0.7	9
92	Excitation mechanism of Er in Si studied with a free-electron laser. Journal of Luminescence, 1998, 80, 291-295.	1.5	2
93	Direct Observation of the Two-Stage Excitation Mechanism of Er in Si. Physical Review Letters, 1998, 81, 4748-4751.	2.9	46
94	Shallow thermal donors associated with H, Al and N in annealed Czochralski silicon distinguished by infrared spectroscopy. Semiconductor Science and Technology, 1997, 12, 1404-1408.	1.0	15
95	Electron-paramagnetic-resonance study of silver-induced defects in silicon. Physical Review B, 1997, 56, 4614-4619.	1.1	8
96	Copper-related defects in silicon: Electron-paramagnetic-resonance identification. Physical Review B, 1997, 56, 4620-4625.	1.1	15
97	Photoluminescence Study of Erbium in Silicon with a Free-Electron Laser. Materials Science Forum, 1997, 258-263, 1497-1502.	0.3	2
98	High-Field EPR Spectroscopy of Thermal Donors in Silicon. Materials Science Forum, 1997, 258-263, 373-378.	0.3	6
99	The 4f Intrashell Transitions of Ytterbium in Indium Phosphide. Materials Research Society Symposia Proceedings, 1996, 422, 161.	0.1	2
100	Excitation and DE-Excitation of Yb³⁺ in Inp and Er³⁺ in Si: Photoluminescence and Impact Ionization Studies. Materials Research Society Symposia Proceedings, 1996, 422, 207.	0.1	10
101	Magnetic resonance spectroscopy of hydrogen-passivated double donors in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 36, 138-141.	1.7	4
102	Infrared absorption in silicon from shallow thermal donors incorporating hydrogen and a link to the NL10 paramagnetic resonance spectrum. Physical Review B, 1996, 54, R6803-R6806.	1.1	49
103	Magnetic Resonance Investigations of Thermal Donors in Silicon. , 1996, , 61-82.		4
104	Magnetic resonance spectroscopy of hydrogen-passivated double donors in silicon. , 1996, , 138-141.		0
105	Endor Identification of a Hydrogen-Passivated Thermal Donor. Materials Science Forum, 1995, 196-201, 849-854.	0.3	12
106	Role of electron traps in the excitation and deâ€excitation mechanism of Yb3+in InP. Journal of Applied Physics, 1995, 77, 1523-1530.	1.1	8
107	Electron paramagnetic resonance versus spin-dependent recombination: Excited triplet states of structural defects in irradiated silicon. Physical Review B, 1995, 52, 1144-1151.	1.1	49
108	Role of Hydrogen in the Formation and Structure of the Si- NL10 Thermal Donor. Physical Review Letters, 1995, 74, 2030-2033.	2.9	57

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109	Electron-paramagnetic-resonance identification of hydrogen-passivated sulfur centers in silicon. Physical Review B, 1995, 51, 16746-16749.	1.1	17
110	Hydrogen Passivation of the Sulfur Double Donor in Silicon Investigated by EPR and ENDOR. Materials Science Forum, 1995, 196-201, 855-860.	0.3	4
111	Photoluminescence measurements on erbium-doped silicon. Semiconductor Science and Technology, 1995, 10, 666-671.	1.0	9
112	Photoluminescence Study of the 779-meV Band in Silver-Doped Silicon. Materials Science Forum, 1994, 143-147, 755-760.	0.3	2
113	Stallinga, Gregorkiewicz, and Ammerlaan Reply. Physical Review Letters, 1994, 73, 1457-1457.	2.9	6
114	EPR spectroscopy of platinum-hydrogen complexes in silcon. Physical Review B, 1994, 49, 13423-13429.	1.1	30
115	Electron paramagnetic resonance study of the NL51 spectrum in hydrogen-implanted silicon. Solid State Communications, 1994, 90, 401-404.	0.9	12
116	Electron paramagnetic resonance of molecular hydrogen in silicon. Physical Review Letters, 1993, 71, 117-120.	2.9	32
117	Photoluminescence of silicon thermal donors. Physical Review B, 1993, 47, 7005-7012.	1.1	21
118	Magnetic resonance spectroscopy in silverâ€doped silicon. Journal of Applied Physics, 1993, 73, 1797-1801.	1.1	13
119	A New Bistable Shallow Thermal Donor in Al-Doped Si. Materials Science Forum, 1993, 143-147, 1185-1190.	0.3	7
120	Trapping of Molecular Hydrogen in Porous Silicon and at Si/SiO2 Interfaces and a Possible Reinterpretation of the Pb Center. Materials Research Society Symposia Proceedings, 1993, 324, 385.	0.1	0
121	Excitation and De-Excitation Mechanisms of Rare-Earth Ions in III-V Compounds: Optically Detected Microwave-Induced Impact Ionization of Yb Dopant in Inp. Materials Research Society Symposia Proceedings, 1993, 301, 239.	0.1	4
122	Silicon Thermal Donors: Photoluminescence and Magnetic Resonance Study of Boron- and Aluminum-Doped Silicon. Materials Science Forum, 1992, 83-87, 407-412.	0.3	2
123	Paramagnetic state of the isolated gold impurity in silicon. Physical Review Letters, 1992, 69, 3185-3188.	2.9	19
124	Electron-paramagnetic-resonance identification of silver centers in silicon. Physical Review B, 1992, 46, 4544-4550.	1.1	27
125	Sensitive electron paramagnetic resonance spectrometer for studying defects in semiconductors. Review of Scientific Instruments, 1992, 63, 5742-5749.	0.6	8
126	Photoluminescence studies on thermal donors in boron- and aluminum-doped silicon. Physical Review B, 1992, 46, 2034-2040.	1.1	11

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127	High-resolution EPR spectroscopy of the Si-NL10 thermal donor. Physical Review B, 1992, 45, 5873-5878.	1.1	3
128	Aluminum incorporation in the Si-NL10 thermal donor. Physical Review B, 1992, 46, 4582-4589.	1.1	7
129	High-field EPR spectroscopy of thermal donors in silicon. Physica B: Condensed Matter, 1992, 177, 476-480.	1.3	1
130	Nuclear interactions of defects in semiconductors â€" magnetic resonance measurements. Nuclear Instruments & Methods in Physics Research B, 1992, 63, 154-162.	0.6	4
131	Infrared Absorption Study of Thermally Generated Shallow Donor Centers in Czochralski Silicon. Acta Physica Polonica A, 1992, 82, 677-680.	0.2	2
132	Optically detected microwaveâ€•induced impact ionization of ytterbium bound excitons in InP. Applied Physics Letters, 1991, 58, 2237-2239.	1.5	25
133	Optically detected Auger recombinations in erbiumâ€•and ytterbiumâ€•doped InP. Applied Physics Letters, 1991, 59, 3279-3281.	1.5	9
134	Magnetic-resonance studies of interstitial Mn in GaP and GaAs. Physical Review B, 1991, 44, 3012-3019.	1.1	28
135	Characterization of Defect Centres in Semiconductors by Advanced ENDOR Techniques. Acta Physica Polonica A, 1991, 80, 161-170.	0.2	3
136	Thermal Donor Generation in Boron- and Aluminium-Doped Czochralski Silicon. Acta Physica Polonica A, 1991, 80, 345-348.	0.2	3
137	Magnetic resonance spectroscopy of zinc doped silicon. Solid State Communications, 1990, 75, 115-120.	0.9	13
138	Metastable thermal donor states in germanium: Identification by electron paramagnetic resonance. Physical Review B, 1990, 42, 9802-9809.	1.1	16
139	Comparative study of Si-NL8 and Si-NL10 thermal-donor-related EPR centers. Physical Review B, 1990, 41, 12628-12636.	1.1	33
140	Silicon electron-nuclear double-resonance study of the NL10 heat-treatment center. Physical Review B, 1989, 39, 1648-1658.	1.1	12
141	Thermal donors and oxygen-related complexes in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 291-297.	1.7	8
142	Si-NL10: Paramagnetic Acceptor State of the Silicon Thermal Donor. Physical Review Letters, 1988, 61, 227-230.	2.9	22
143	Microscopic structure of the NL10 heat-treatment center in silicon: Study by electron-nuclear double resonance. Physical Review B, 1988, 38, 3998-4015.	1.1	47
144	Transition metal impurities in silicon. , 1988, , 244-261.		4

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145	Photoluminescence on oxygen-rich acceptor-doped silicon. Journal of Physics C: Solid State Physics, 1987, 20, 2183-2191.	1.5	5
146	Electronâ€paramagneticâ€resonance study of heatâ€treatment centers innâ€type silicon. Journal of Applied Physics, 1987, 62, 4404-4405.	1.1	19
147	EPR studies of heat-treatment centers inp-type silicon. Physical Review B, 1987, 35, 3810-3817.	1.1	49
148	Oxygen incorporation in thermal-donor centers in silicon. Physical Review Letters, 1987, 59, 1702-1705.	2.9	28
149	Spin delocalization of interstitial iron in silicon. Physical Review B, 1986, 34, 4511-4520.	1.1	13
150	Oxygen related mechanism of reverse annealing for boron implants in silicon. Radiation Effects, 1984, 85, 249-254.	0.4	2
151	Electron paramagnetic resonance of silicon implanted with boron and arsenic ions. Radiation Effects, 1983, 77, 195-203.	0.4	1
152	EPR studies of the annealing of damage produced by boron implantation of silicon single crystals. Radiation Effects, 1982, 68, 69-76.	0.4	1